



DMP3098LDM

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low R_{DS(ON)}:
 - 65mΩ @V_{GS} = -10V ٠
 - 115mΩ @V_{GS} = -4.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

Mechanical Data

- Case: SOT-26 •
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See page 4
- Weight: 0.008 grams (approximate) .

TOP VIEW



Internal Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current (Note 1) Continuous	T _A = 25°C T _A = 70°C	ID	-4.0 -3.0	А	
Pulsed Drain Current (Note 2)		I _{DM}	-14	А	

SOT-26

Thermal Characteristics

Notes:

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	PD	1.25	W
Thermal Resistance, Junction to Ambient (Note 1); Steady-State	$R_{ heta}$ JA	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

1. Device mounted on 1"x1", FR-4 PC board on 0.1in.² pads on 2 oz. Copper pads and test pulse width $t \le 10s$. 2. Repetitive Rating, pulse width limited by junction temperature.

3. No purposefully added lead.

4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition		
STATIC PARAMETERS	• • • • • • • • • • • • • • • • • • • •		• 7 P		•			
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	I _D = -250μA, V _{GS} = 0V		
Zero Gate Voltage Drain Current $T_J = 25^{\circ}$				-1	μA	V _{DS} = -30V, V _{GS} = 0V		
Gate-Body Leakage Current	I _{GSS}	_	_	±100	nA	V _{DS} = 0V, V _{GS} = ±20V		
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	-2.1	V	V _{DS} = V _{GS} , I _D = -250μA		
On State Drain Current (Note 5)	I _{D (ON)}	-15		_	Α	V _{GS} = -4.5V, V _{DS} = -5V		
Static Drain-Source On-Resistance (Note 5)	R _{DS (ON)}	_	56 98	65 115	mΩ	V _{GS} = -10V, I _D = -4.0A V _{GS} = -4.5V, I _D = -3.0A		
Forward Transconductance (Note 5)	g FS		5.3		S	$V_{\rm DS} = -10V, I_{\rm D} = -4.0A$		
Diode Forward Voltage (Note 5)	V _{SD}	_	0.79	-1.2	V	$I_{\rm S} = -1.7$ A, $V_{\rm GS} = 0$ V		
DYNAMIC PARAMETERS (Note 6)	00		1	•	1			
Input Capacitance	Ciss	_	336	_	pF			
Output Capacitance	Coss	_	70	_	pF	V _{DS} = -25V, V _{GS} = 0V f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	49	_	pF			
Gate Resistance	R _G	_	4.6		Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz		
SWITCHING CHARACTERISTICS								
Total Gate Charge Gate-Source Charge		_	4.0 7.8	—	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -5.0A V _{DS} = -15V, V _{GS} = -10V, I _D = -5.0A		
			1.0	_		V _{DS} = -15V, V _{GS} = -4.5V, I _D = -5.0A		
Gate-Drain Charge	Q _{gs} Q _{qd}		2.5	_		V _{DS} = -15V, V _{GS} = -4.5V, I _D = -5.0A		
Turn-On Delay Time	t _{d(on)}		6.0	—				
Rise Time	tr		5.0	_	ns	V _{DS} = -15V, V _{GS} = -10V,		
Turn-Off Delay Time	t _{d(off)}		17.6	_	115	I _D = -1.0A, R _G = 6.0Ω		
Fall Time	tf	_	9.5	_				

Notes: 5. Test pulse width t = 300μ s.

6. Guaranteed by design. Not subject to production testing.







DMP3098LDM

150°C





0.8 -V_{SD}, SOURCE-DRAIN VOLTAGE (V) Fig. 8 Diode Forward Voltage vs. Current

1

0.6

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Ordering Information (Note 7)

Part Number	Case	Packaging
DMP3098LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



DMB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date	Code	Kev

EW PRODUCT

Vate Code Key Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
С	2.40
E	0.95

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